



Peak pulse voltage ($T_j=25$; non-repetitive, off-state; FIG.7)	V_{pp}	4	kV
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ELECTRICAL CHARACTERISTICS ($T_j=25$ unless otherwise specified)

Symbol	Test Condition	Quadrant	Value		Unit
I_{GT}	$V_D=12V$ $R_L=33\Omega$	- -	MAX.	10	mA
V_{GT}		- -	MAX.	1	V
V_{GD}	$V_D=V_{DRM}$ $T_j=125$ $R_L=3.3k\Omega$	- -	MIN.	0.2	V
I_L	$I_G=1.2I_{GT}$	-	MAX.	20	mA
				30	
I_H	$I_T=100mA$		MAX.	15	mA
dV/dt	$V_D=540V$ Gate Open $T_j=125$		MIN.	500	V/ μs
$(dI/dt)_c$	$(dV/dt)_c=10V/\mu s$ $T_j=125$		MIN.	1.5	A/ms
t_{on} t	$I_G=20mA$ $I_A=200mA$ $I_R=20mA$ $T_j=25$		TYP.	2.5	μs



ORDERING INFORMATION

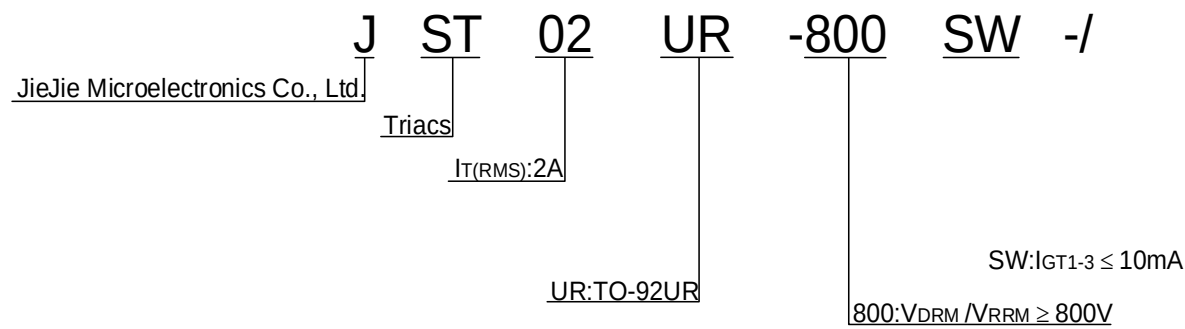




FIG.1: Maximum power dissipation versus RMS on-state current

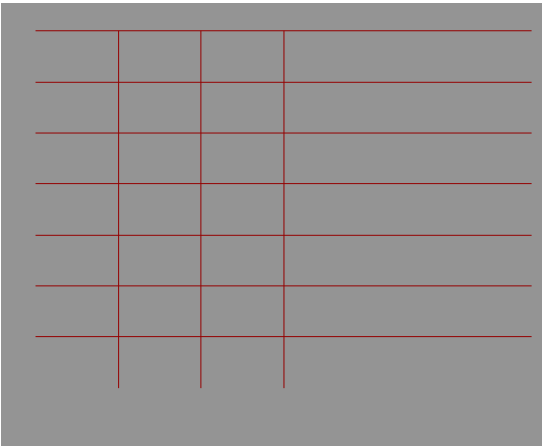


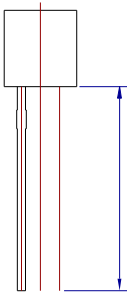
FIG.2: RMS on-state current versus case temperature

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PACKAGE MECHANICAL DATA





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